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ISSUE CLASSIFICATION	
Class	Subclass

PATENT NUMBER

U.S. **UTILITY** Patent Application

O.I.P.E.		PATENT DATE
SCANNED <i>17c3</i>	Q.A. <i>SP1</i>	

APPLICATION NO. 09/902497	CONT/PRIOR D F	CLASS 427	SUBCLASS	ART UNIT 1762	EXAMINER A/...
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APPLICANTS

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STUDY

Method of epitaxy on a silicon substrate comprising areas heavily doped with arsenic

PTO-2040
12/89[illegible]

<input type="checkbox"/> TERMINAL DISCLAIMER	DRAWINGS		CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims
<input type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed. <input type="checkbox"/> The term of this patent shall not extend beyond the expiration date of U.S Patent. No. _____ 	_____ (Assistant Examiner) (Date)		NOTICE OF ALLOWANCE MAILED	
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			Amount Due	Date Paid
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